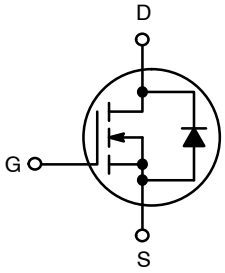
MOSFET – Power, N-Channel, SUPERFET III, Easy-Drive

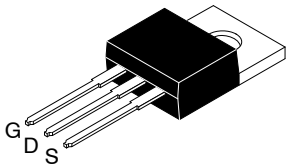
650 V, 19 A, 165 mΩ

FCP165N65S3

V_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX
650 V	165 mΩ @ 10 V	19 A



POWER MOSFET



TO−220
CASE 340AT

Description

SUPERFET III MOSFET is **onsemi**'s brand−new high voltage super−junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on−resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provides superior switching performance, and withstand extreme dv/dt rate. Consequently, SUPERFET III MOSFET Easy−drive series helps manage EMI issues and allows for easier design implementation.

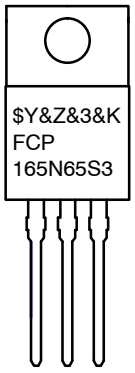
Features

- 700 V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 140 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 39 nC)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)}$ = 341 pF)
- 100% Avalanche Tested
- These Devices are Pb−Free and are RoHS Compliant

Applications

- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Industrial Power Supplies
- Lighting / Charger / Adapter

MARKING DIAGRAM



$Y	= **onsemi** Logo
&Z	= Assembly Plant Code
&3	= Data Code (Year & Week)
&K	= Lot
FCP165N65S3	= Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
FCP165N65S3	TO−220−3	800 Units / Tube

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		650	V
V_{GSS}	Gate to Source Voltage	– DC	±30	V
		– AC (f > 1 Hz)	±30	
I_D	Drain Current	– Continuous (T_C = 25°C)	19	A
		– Continuous (T_C = 100°C)	12.3	
I_{DM}	Drain Current	– Pulsed (Note 1)	47.5	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		87	mJ
I_{AS}	Avalanche Current (Note 2)		2.7	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		1.54	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		20	
P_D	Power Dissipation	(T_C = 25°C)	154	W
		– Derate Above 25°C	1.23	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		–55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8″ from Case for 5 seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse−width limited by maximum junction temperature.
2. I_{AS} = 2.7 A, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 9.5 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.81	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	V_{GS} = 0 V, I_D = 1 mA, T_J = 25°C	650			V
		V_{GS} = 0 V, I_D = 1 mA, T_J = 150°C	700			V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 1 mA, Referenced to 25°C		0.64		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650 V, V_{GS} = 0 V			1	μA
		V_{DS} = 520 V, T_C = 125°C		0.85		
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±30 V, V_{DS} = 0 V			±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 0.44 mA	2.5		4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 9.5 A		140	165	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 20 V, I_D = 9.5 A		12		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 400 V, V_{GS} = 0 V, f = 1 MHz		1500		pF
C_{oss}	Output Capacitance			35		pF
$C_{oss(eff.)}$	Effective Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V		341		pF
$C_{oss(er.)}$	Energy Related Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V		49		pF
$Q_{g(tot)}$	Total Gate Charge at 10 V	V_{DS} = 400 V, I_D = 9.5 A, V_{GS} = 10 V (Note 4)		39		nC
Q_{gs}	Gate to Source Gate Charge			11		nC
Q_{gd}	Gate to Drain “Miller” Charge			16		nC
ESR	Equivalent Series Resistance	f = 1 MHz		4.6		Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400 V, I_D = 9.5 A, V_{GS} = 10 V, R_g = 4.7 Ω (Note 4)		21		ns
t_r	Turn-On Rise Time			22		ns
$t_{d(off)}$	Turn-Off Delay Time			53		ns
t_f	Turn-Off Fall Time			13		ns
SOURCE-DRAIN DIODE CHARACTERISTICS						
I_S	Maximum Continuous Source to Drain Diode Forward Current				19	A
I_{SM}	Maximum Pulsed Source to Drain Diode Forward Current				47.5	A
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 9.5 A			1.2	V
t_{rr}	Reverse Recovery Time	V_{DD} = 400 V, I_{SD} = 9.5 A, dI_F/dt = 100 A/μs		339		ns
Q_{rr}	Reverse Recovery Charge			5.8		μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

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TYPICAL PERFORMANCE CHARACTERISTICS

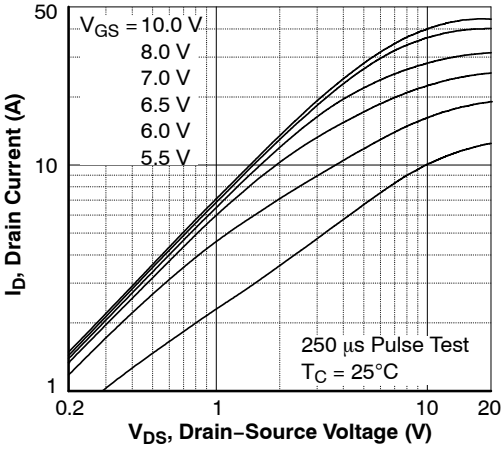

Figure 1. On−Region Characteristics

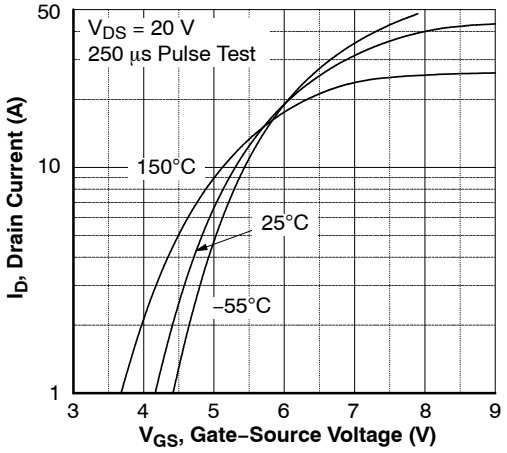

Figure 2. Transfer Characteristics

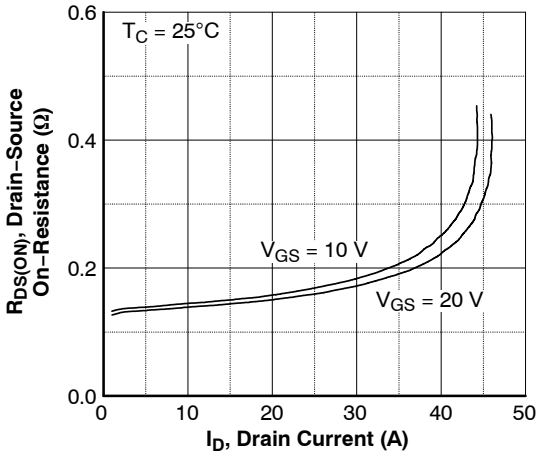

Figure 3. On−Resistance Variation vs. Drain Current and Gate Voltage

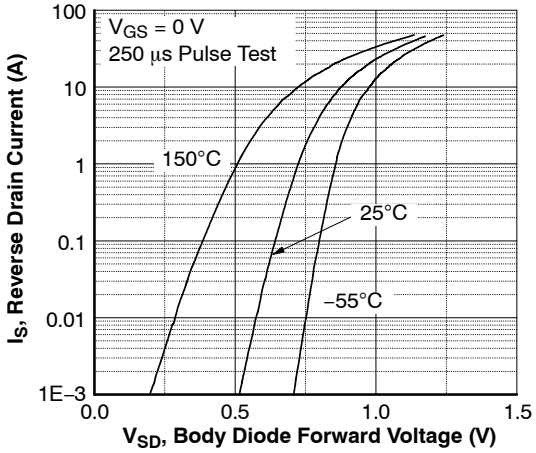

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

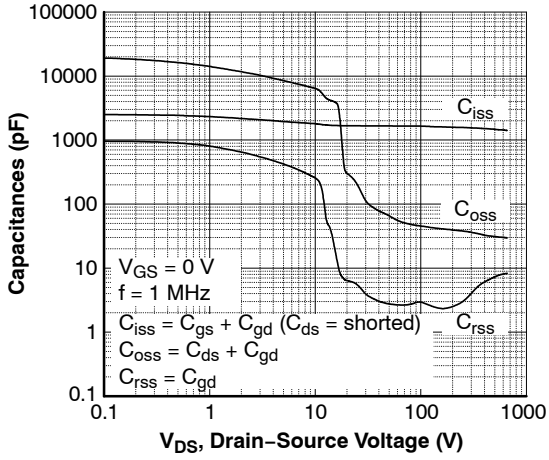

Figure 5. Capacitance Characteristics

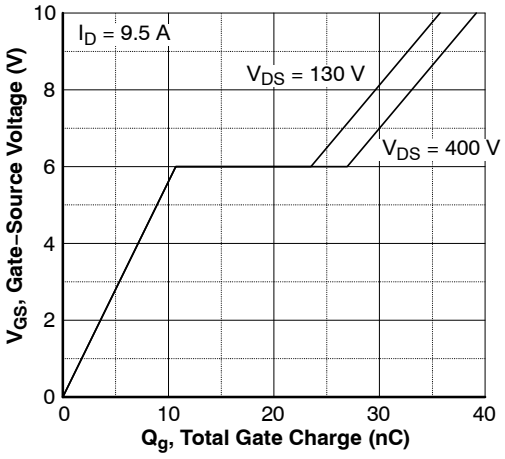

Figure 6. Gate Charge Characteristics

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TYPICAL PERFORMANCE CHARACTERISTICS (continued)

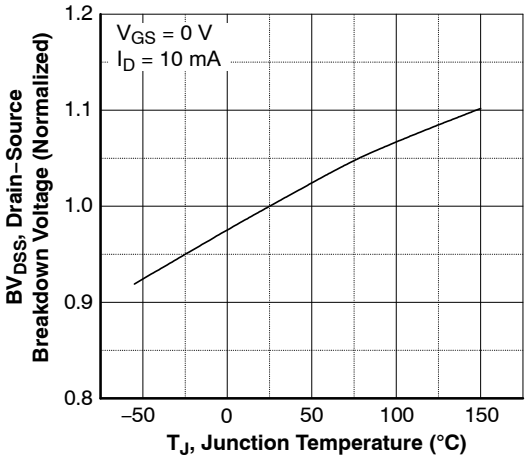

Figure 7. Breakdown Voltage Variation vs. Temperature

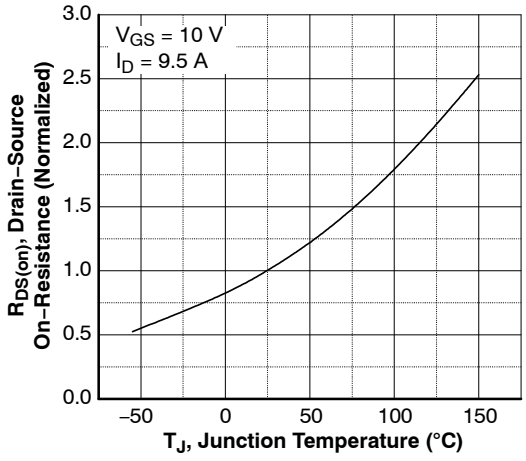

Figure 8. On−Resistance Variation vs. Temperature

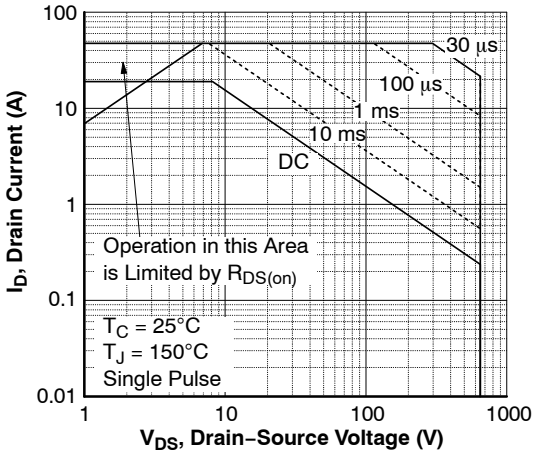

Figure 9. Maximum Safe Operating Area

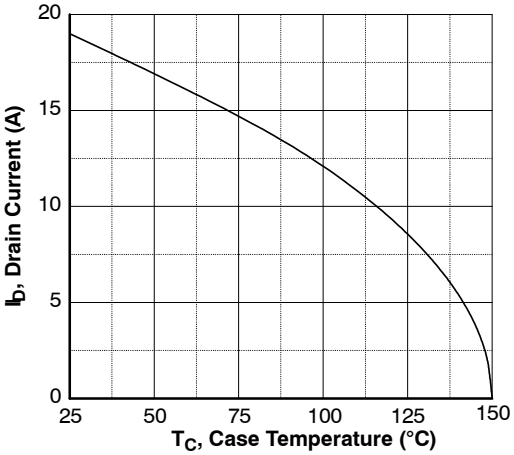

Figure 10. Maximum Drain Current vs. Case Temperature

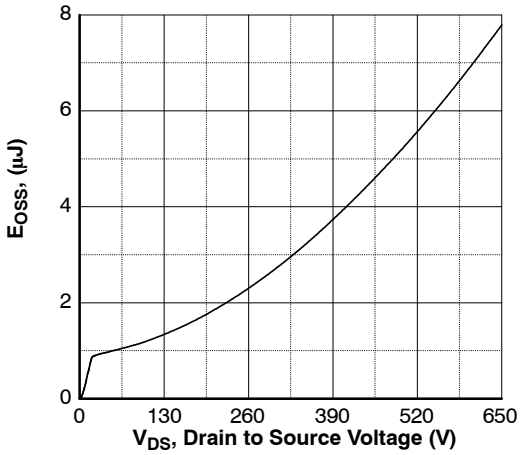

Figure 11. E_{OSS} vs. Drain to Source Voltage

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TYPICAL PERFORMANCE CHARACTERISTICS (continued)

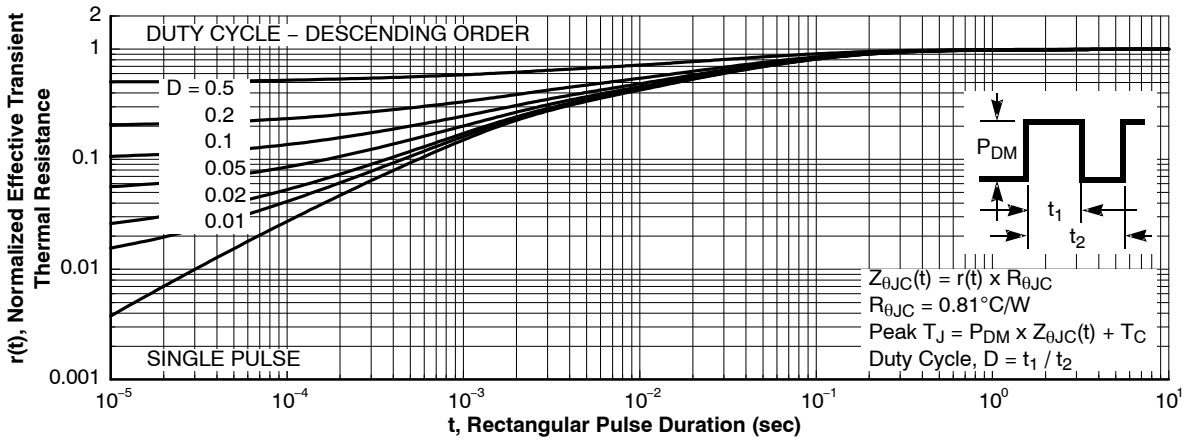

Figure 12. Transient Thermal Response Curve

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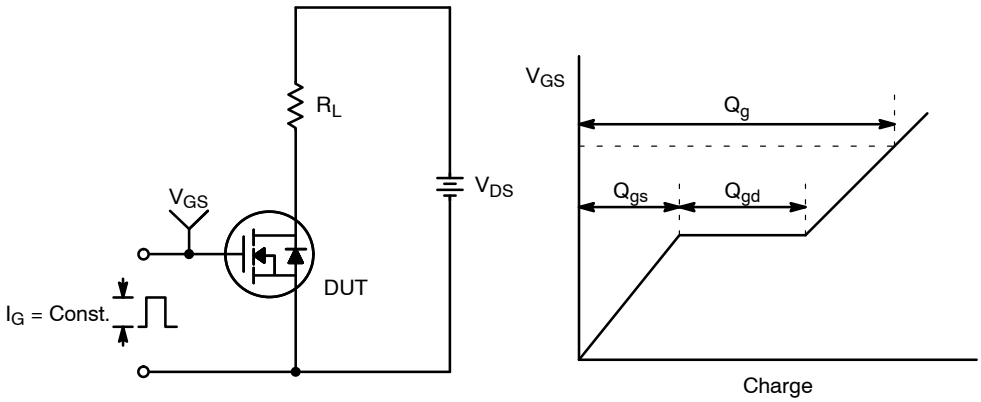

Figure 13. Gate Charge Test Circuit & Waveform

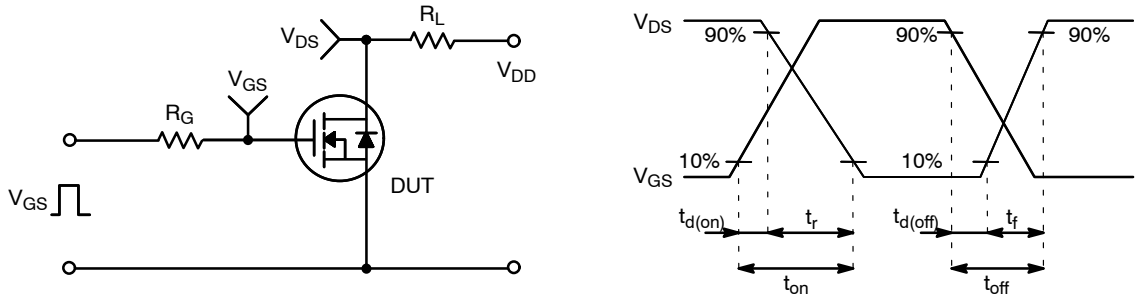

Figure 14. Resistive Switching Test Circuit & Waveforms

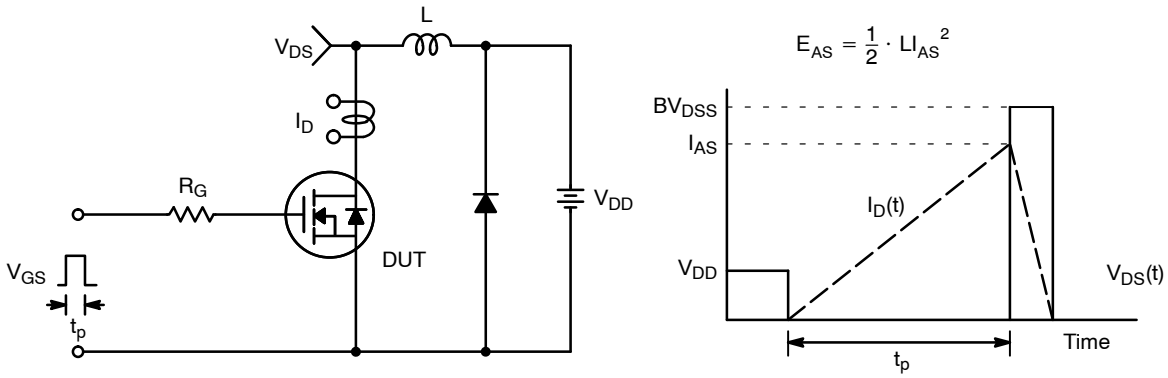

Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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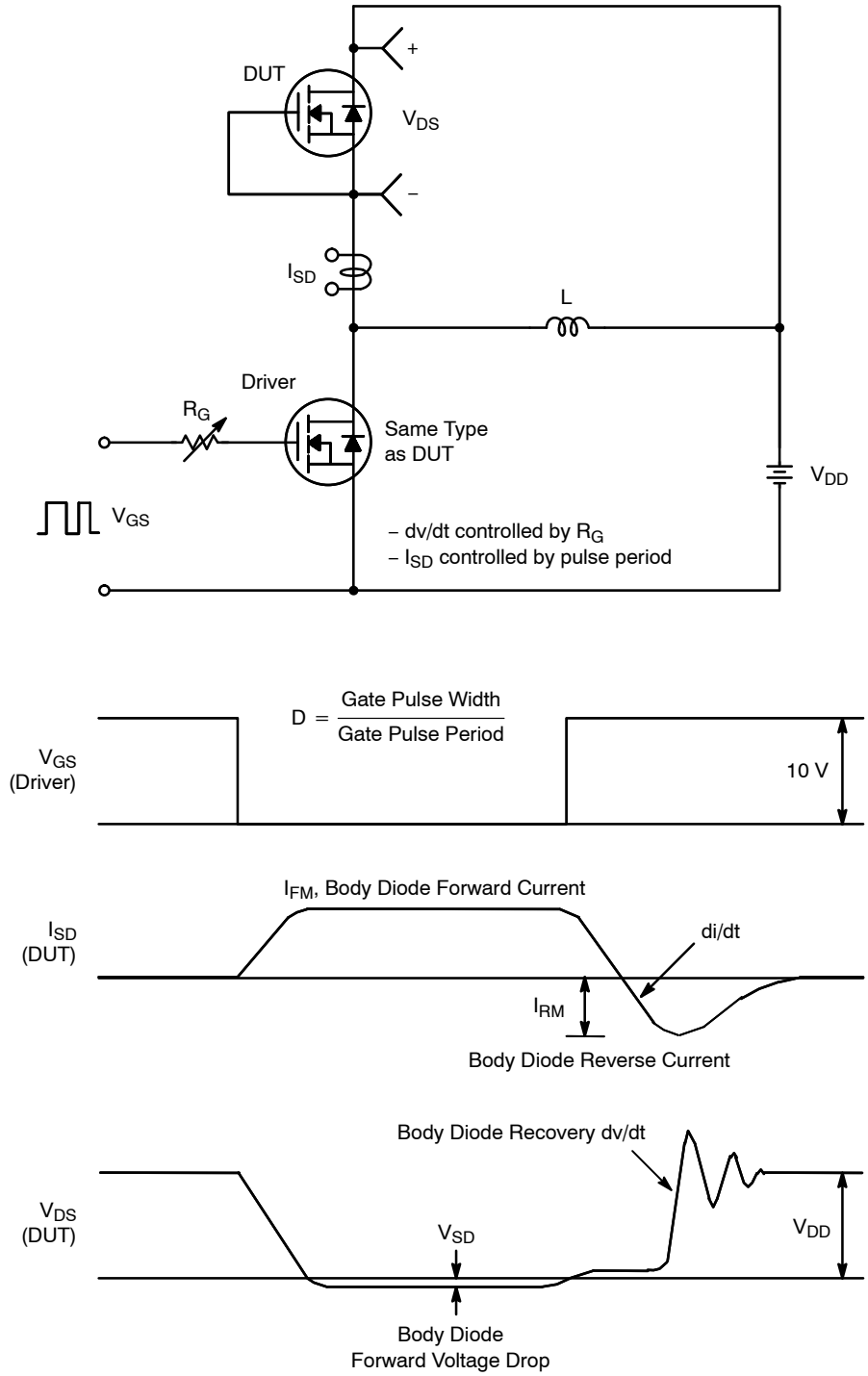

Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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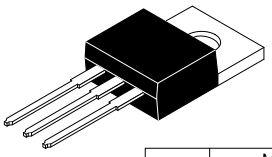
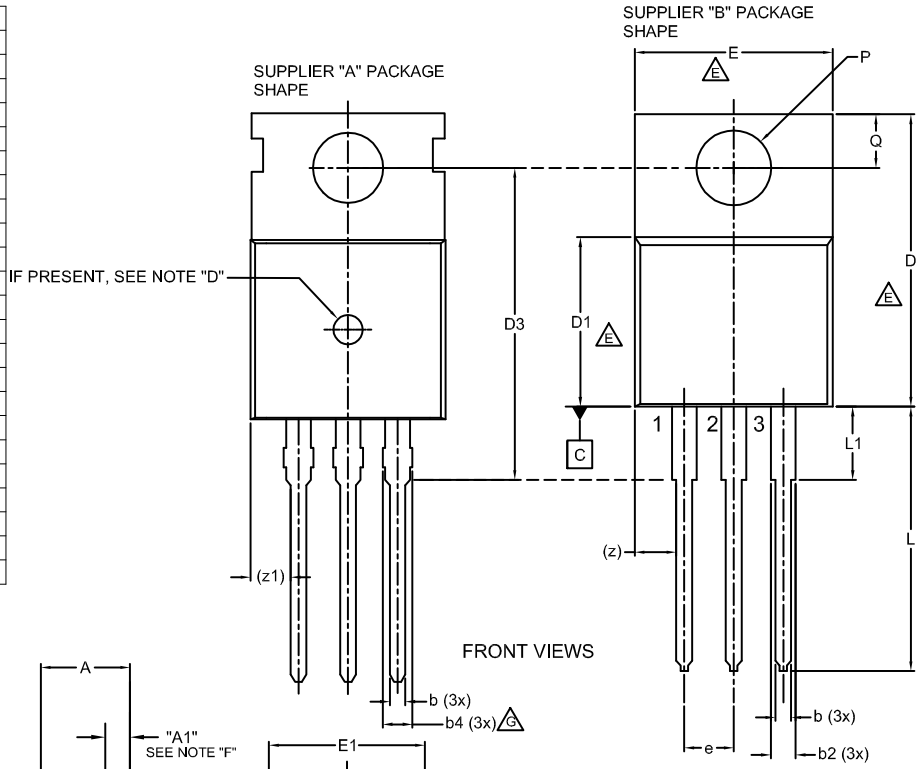
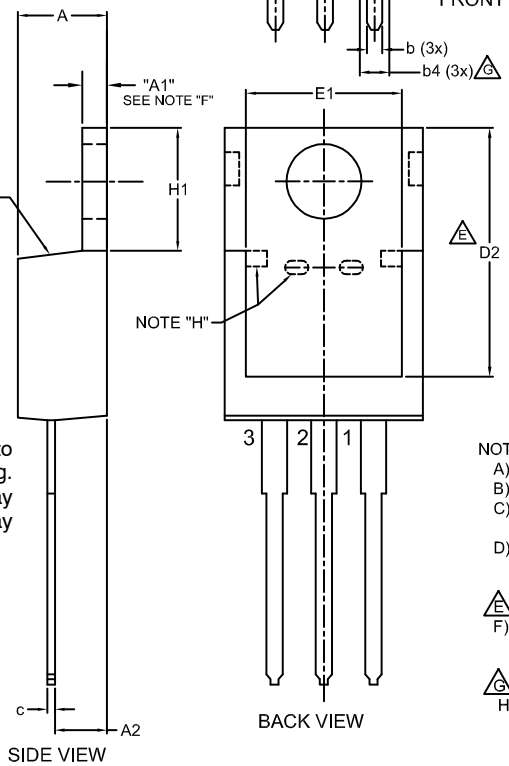


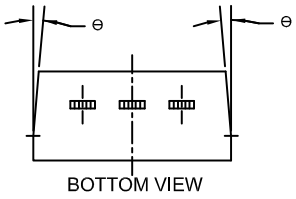
TO−220−3LD
CASE 340AT
ISSUE B

DATE 08 AUG 2022

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.00	--	4.70
A1	SEE NOTE "F"		
A2	2.10	--	2.85
b	0.55	--	1.00
b2	1.10	--	1.62
b4	1.42	--	1.62
c	0.36	--	0.60
D	13.90	--	16.30
D1	8.13	--	9.40
D2	11.50	--	14.30
D3	15.42	--	16.51
E	9.65	--	10.67
E1	7.59	--	8.65
e	2.40	--	2.67
H1	6.06	--	6.69
L	12.70	--	14.04
L1	2.70	--	4.10
P	3.50	--	4.00
Q	2.50	--	3.40
z	2.13 REF		
z1	2.06 REF		
Θ	3°	–	5°







GENERIC MARKING DIAGRAM*

XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

NOTES:
A) REFERENCE JEDEC, TO-220, VARIATION AB
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [ ].
D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
E) DOES NOT COMPLY JEDEC STANDARD VALUE.
F) "A1" DIMENSIONS AS BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1.10 - 1.45
G) PRESENCE IS SUPPLIER DEPENDENT
H) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

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DESCRIPTION:	**TO−220−3LD**		**PAGE 1 OF 1**

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